

FAN5109

Dual Bootstrapped 12V MOSFET Driver

Features

- Drives N-channel High-Side and Low-Side MOSFETs in a Synchronous Buck Configuration
- Enhanced Upgrade to FAN5009
- Direct Interface to FAN5019B/FAN5182 and other compatible PWM Controllers
- 12V High-Side and 12V Low-Side Drive
- Internal Adaptive "Shoot-Through" Protection
- Fast Rise and Fall times
- Switching Frequency above 500kHz
- $\overline{OD}$ input for Output Disable – allows for synchronization with PWM Controller
- SOIC-8 Package

Applications

- Multi-phase VRM/VRD Regulators for Microprocessor Power
- High Current/High Frequency DC/DC Converters
- High Power Modular Supplies

General Description

The FAN5109 is a high-frequency driver, specifically designed to drive N-Channel power MOSFETs in a synchronous-rectified buck converter. This driver, combined with a Fairchild Multi-Phase PWM controller and power MOSFETs, form a complete core voltage regulator solution for advanced microprocessors.

The FAN5109 drives the upper and lower MOSFET gates of a synchronous buck regulator up to $12V_{GS}$. The FAN5109's output drivers can efficiently switch power MOSFETs at frequencies above 500kHz. The circuit's adaptive shoot-through protection prevents the MOSFETs from conducting simultaneously.

The FAN5109 is rated for operation from 0°C to $+85^{\circ}\text{C}$ and is available in a low-cost SOIC-8 package.

Ordering Information

Part Number	Temperature Range	Pb-Free	Package	Packing	Qty/Reel
FAN5109MX	0°C to 85°C	Yes	SOIC-8	Tape and Reel	2500

Note: Contact Fairchild Sales for availability of leaded parts.

Typical Application

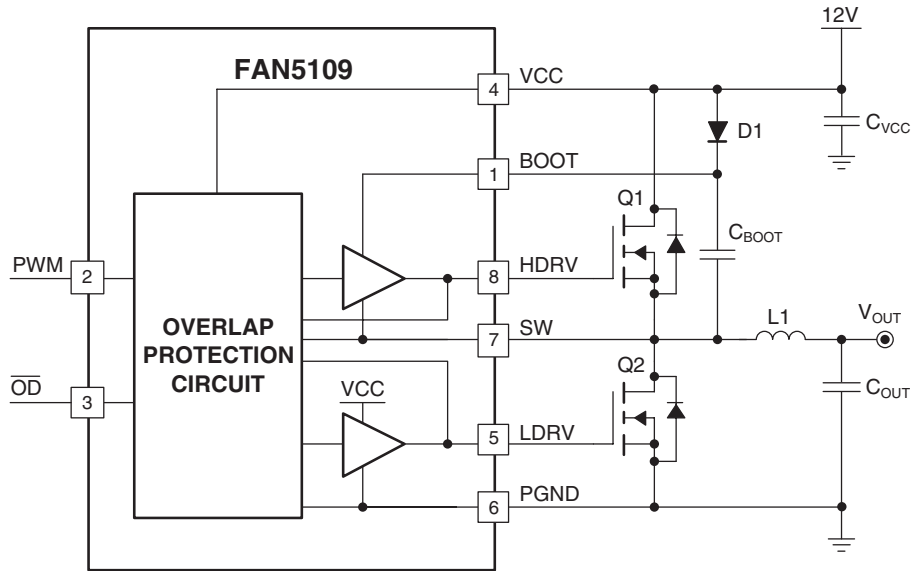


Figure 1. Typical Application

Pin Configuration

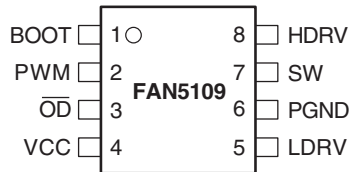


Figure 2. 8-Pin SOIC Package

Pin Definitions

Pin #	Pin Name	Pin Function Description
1	BOOT	Bootstrap Supply Input. Provides voltage supply to the high-side MOSFET driver. Connect to bootstrap capacitor and diode.
2	PWM	PWM Signal Input. Accepts a logic-level PWM signal from the controller.
3	OD	Output Disable. When low, this pin disables FET switching (HDRV and LDRV are held low).
4	VCC	Power Input. +12V bias power. Bypass with a 1μF ceramic capacitor.
5	LDRV	Low Side Gate Drive Output. Connect to the gate of the low-side power MOSFET(s).
6	PGND	Power Ground. Connect directly to the source of low-side MOSFET(s) and C_VCC.
7	SW	Switch Node Input. Connect as shown in Figure 1. SW provides return for the high-side bootstrapped driver and acts as a sense point for the adaptive shoot-thru protection.
8	HDRV	High Side Gate Drive Output. Connect to the gate of the high-side power MOSFET(s).

Functional Block Diagram

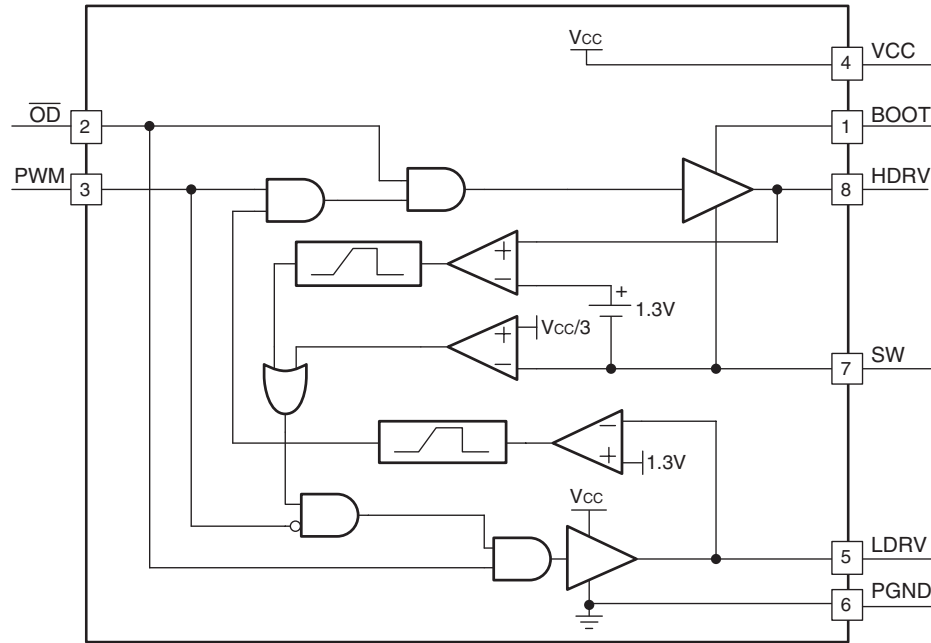


Figure 3. Functional Block Diagram

Absolute Maximum Ratings

Stresses above those listed in “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or other conditions beyond those indicated in the operational section of this specification is not implied. Exposure to the absolute maximum rating conditions for extended periods may affect device reliability. Absolute maximum ratings apply individually, not in combination. Unless otherwise specified, voltages are referenced to PGND.

Parameter		Min.	Max.	Unit
VCC to PGND		−0.3	15	V
PWM and $\overline{\text{OD}}$ pins		−0.3	5.5	V
SW to PGND	Continuous	−1	15	V
	Transient ($t=100\text{nsec}$, $F \leq 500\text{kHz}$)	−5 ⁽¹⁾	25	V
BOOT to SW		−0.3	15	V
BOOT to PGND	Continuous	−0.3	30	V
	Transient ($t=100\text{nsec}$, $F \leq 500\text{kHz}$)		38 ⁽¹⁾	V
HDRV		$V_{\text{SW}}-1$	$V_{\text{BOOT}}+0.3$	V
LDRV	Continuous	−0.5	V_{CC}	V
	Transient ($t=200\text{nsec}$)	−2 ⁽¹⁾	$V_{\text{CC}}+0.3$	V

Notes:

- For transient derating beyond the levels indicated, refer to the graphs on page 9.

Thermal Information

Parameter	Min.	Typ.	Max.	Unit
Junction Temperature (T_J)	0		150	°C
Storage Temperature	−65		150	°C
Lead Soldering Temperature, 10 seconds			300	°C
Vapor Phase, 60 seconds			215	°C
Infrared, 15 seconds			220	°C
Power Dissipation (P_D) $T_A = 25^\circ\text{C}$			715	mW
Thermal Resistance, SO8 – Junction to Case θ_{JC}		40		°C/W
Thermal Resistance, SO8 – Junction to Ambient θ_{JA}		140		°C/W

Recommended Operating Conditions

Parameter	Conditions	Min.	Typ.	Max.	Unit
Supply Voltage V_{CC}	V_{CC} to PGND	10	12	13.5	V
Ambient Temperature (T_A)		0		85	°C
Junction Temperature (T_J)		0		125	°C

Electrical Specifications

$V_{CC} = 12V$, and $T_A = 25^\circ C$ using the circuit in Figure 4 unless otherwise noted. The • denotes specifications which apply over the full operating temperature range.

Parameter	Symbol	Conditions		Min.	Typ.	Max.	Unit
Input Supply							
VCC Voltage Range	V _{CC}		•	6.4	12	13.5	V
VCC Current	I _{CC}	OD = 0V	•		2.5	4	mA
OD Input							
Input High Voltage	V _{IH} (OD)		•	2.5			V
Input Low Voltage	V _{IL} (OD)		•			0.8	V
Input Hysteresis			•		550		mV
Input Current	I _{OD}	OD = 3.0V	•	−300		+300	nA
Propagation Delay ²	t _{pdl} (OD)	See Figure 5			25	40	ns
	t _{pdh} (OD)				15	30	ns
PWM Input							
Input High Voltage	V _{IH} (PWM)		•	3.5			V
Input Low Voltage	V _{IL} (PWM)		•			0.8	V
Input Current	I _{IL} (PWM)		•	-1		+1	μA
High-Side Driver							
Output Resistance, Sourcing	R _{HUP}	V _{BOOT} − V _{SW} = 12V			2.5	3.3	Ω
Source Current ²		V _{DS} = -10V			2.0		A
Output Resistance, Sinking	R _{HDN}	V _{BOOT} − V _{SW} = 12V			1.1	1.5	Ω
Sink Current ²		V _{DS} = 10V			3.0		A
Transition Times ^{2,4}	t _R (HDRV)	Figure 4			25	40	ns
	t _F (HDRV)				15	25	ns
Propagation Delay ^{2,3}	t _{pdh} (HDRV)	See Figure 6			40	55	ns
	t _{pdl} (HDRV)				25	40	ns
Low-Side Driver							
Output Resistance, Sourcing	R _{LUP}				2.0	2.6	Ω
Source Current ²		V _{DS} = -10V			2.7		A
Output Resistance, Sinking	R _{LDN}				0.9	1.2	Ω
Sink Current ²		V _{DS} = 10V			3.5		A
Transition Times ^{2,4}	t _R (LDRV)	Figure 4			20	30	ns
	t _F (LDRV)				15	25	ns
Propagation Delay ^{2,3}	t _{pdh} (LDRV)	See Figure 6			20	30	ns
	t _{pdl} (LDRV)				15	25	ns
		t _{pdh} (LDF)	See Adaptive Gate Drive Circuit description (page 10)			160	

Notes:

1. All limits at operating temperature extremes are guaranteed by design, characterization and statistical quality control.
2. Specifications guaranteed by design/characterization (not production tested).
3. For propagation delays, "tpdh" refers to low-to-high signal transition and "tpdl" refers to high-to-low signal transition.
4. Transition times are defined for 10% and 90% of DC values.

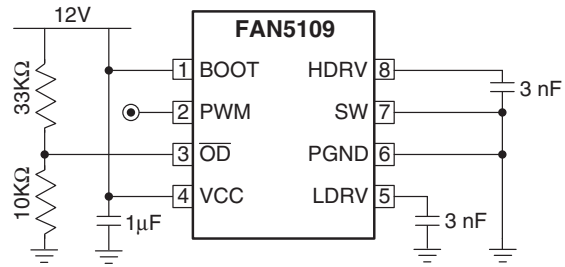


Figure 4. Test Circuit

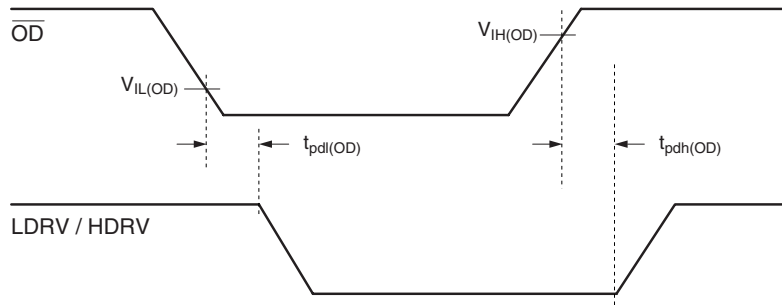


Figure 5. Output Disable Timing

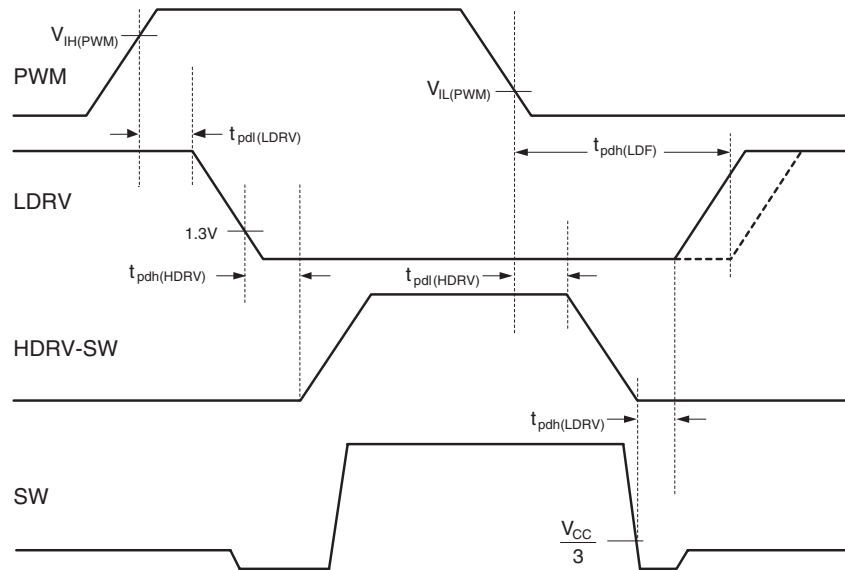
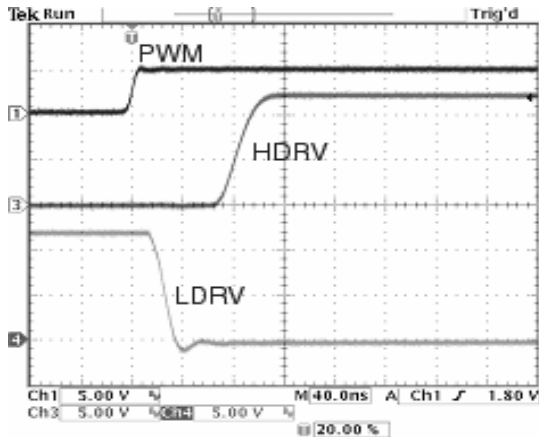
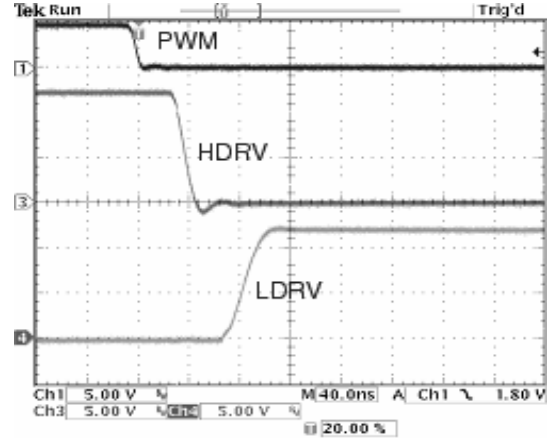


Figure 6. Adaptive Gate Drive Timing

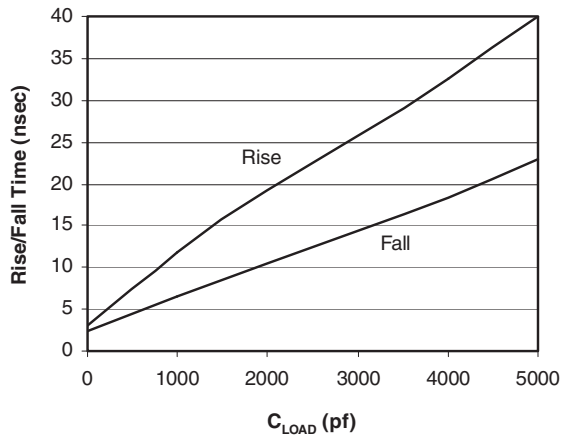
Typical Characteristics



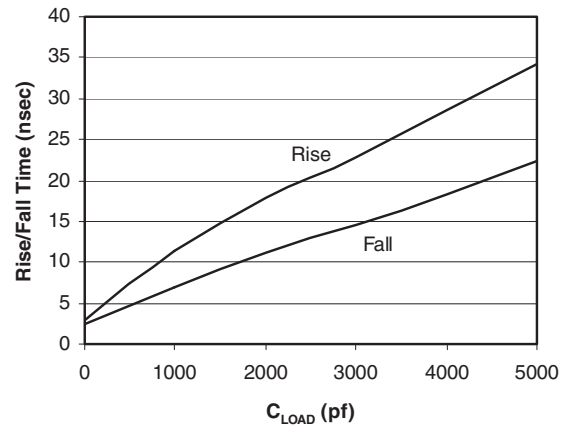
Gate Drive Rise and Fall Times (1)



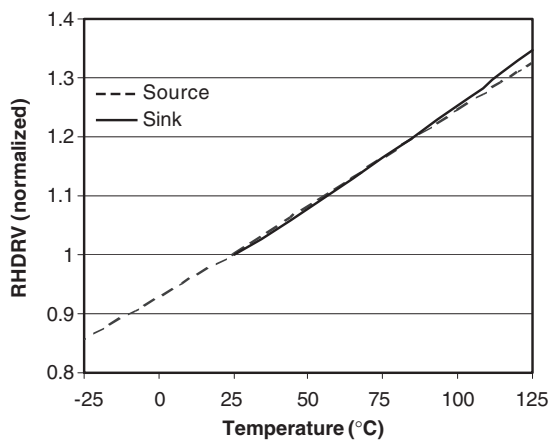
Gate Drive Rise and Fall Times (2)



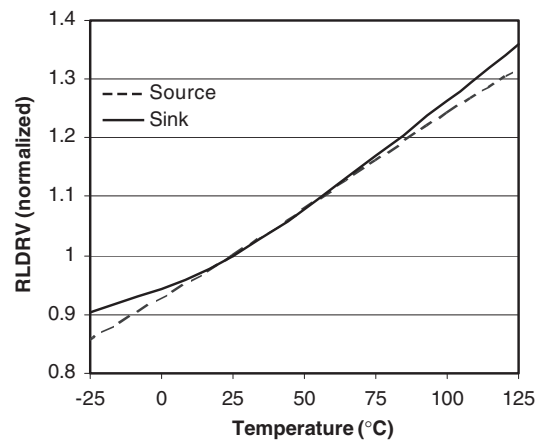
HDRV Rise/Fall Times vs. C_{LOAD}



LDRV Rise/Fall Times vs. C_{LOAD}

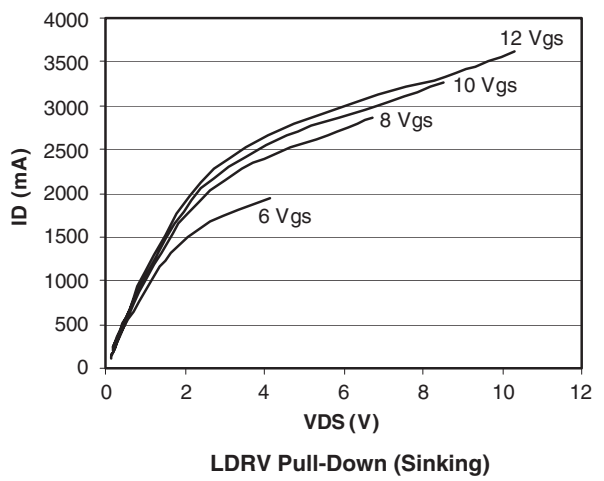
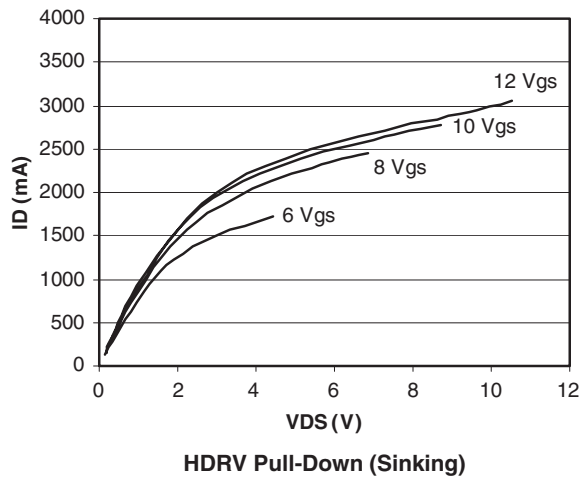
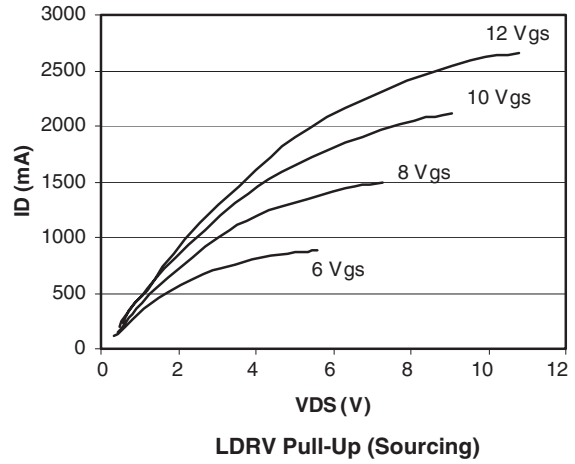
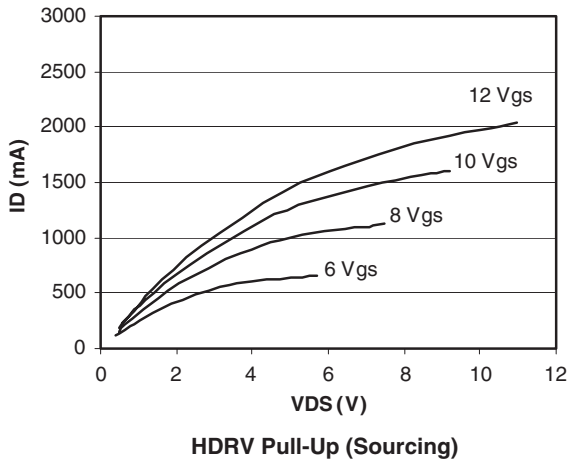


HDRV Normalized Impedance vs. Temperature

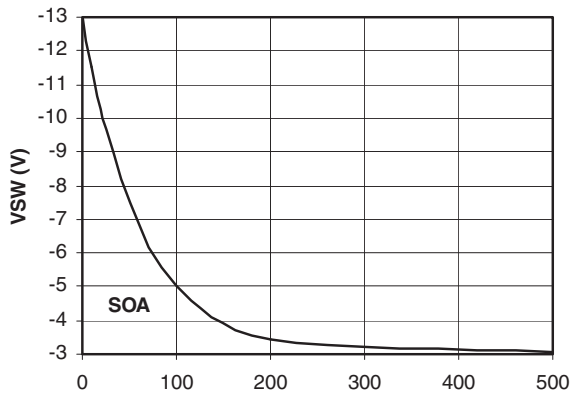


LDRV Normalized Impedance vs. Temperature

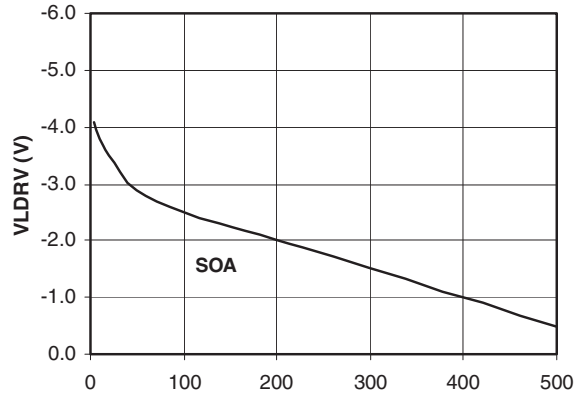
Typical Performance Characteristics (continued)



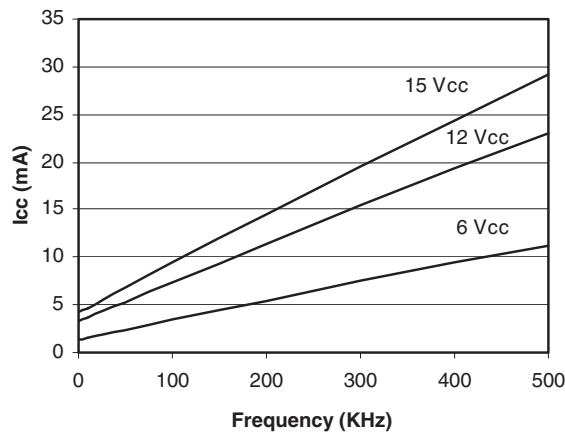
Typical Performance Characteristics (continued)



Negative SW Voltage Transient



Negative LDRV Voltage Transient



Operating Current vs. Frequency
 $I_{CC} [mA] = V_{CC} (0.26 + 3.38 F_{SW})$ where F_{SW} is in MHz

Circuit Description

The FAN5109 is a driver optimized for driving N-channel MOSFETs in a synchronous buck converter topology. A single PWM input signal is all that is required to properly drive the high-side and the low-side MOSFETs.

For a more detailed description of the FAN5109 and its features, refer to the Typical Application Diagram (Figure 1) and Functional Block Diagram (Figure 3).

Low-Side Driver

The FAN5109's low-side driver (LDRV) is designed to drive ground referenced low $R_{DS(on)}$ N-channel MOSFETs. The bias for LDRV is internally connected between V_{CC} and PGND. When the driver is enabled, the driver's output is 180° out of phase with the PWM input. When the FAN5109 is disabled ($\overline{OD} = 0V$), LDRV is held low.

High-Side Driver

The FAN5109's high-side driver (HDRV) is designed to drive a floating N-channel MOSFET. The bias voltage for the high-side driver is developed by a bootstrap supply circuit, consisting of an external diode and bootstrap capacitor (C_{BOOT}).

During start-up, SW is held at PGND, allowing C_{BOOT} to charge to V_{CC} through the diode. When the PWM input goes high, HDRV will begin to charge the high-side MOSFET's gate (Q1). During this transition, charge is transferred from C_{BOOT} to Q1's gate. As Q1 turns on, SW rises to V_{IN} , forcing the BOOT pin to $V_{IN} + V_{C(BOOT)}$, which provides sufficient V_{GS} enhancement for Q1.

To complete the switching cycle, Q1 is turned off by pulling HDRV to SW. C_{BOOT} is then recharged to V_{CC} when SW falls to PGND.

HDRV output is in phase with the PWM input. When the driver is disabled, the high-side gate is held low.

Adaptive Gate Drive Circuit

The FAN5109 embodies an advanced design that ensures minimum MOSFET dead-time while eliminating potential shoot-through (cross-conduction) currents. It senses the state of the MOSFETs and adjusts the gate drive, adaptively, to ensure they do not conduct simultaneously. Refer to "Gate Drive Rise and Fall Times" waveforms on page 7 for the relevant timing information.

To prevent overlap during the low-to-high switching transition (Q2 OFF to Q1 ON), the adaptive circuitry monitors the voltage at the LDRV pin. When the PWM signal goes HIGH, Q2 will begin to turn OFF after some propagation delay as defined by $t_{pdl(LDRV)}$ parameter. Once the LDRV pin is discharged below $\sim 1.3V$, Q1 begins to turn ON after adaptive delay $t_{pdh(HDRV)}$.

To preclude overlap during the high-to-low transition (Q1 OFF to Q2 ON), the adaptive circuitry monitors the voltage at the SW pin. When the PWM signal goes LOW, Q1 will begin to turn OFF after some propagation delay

($t_{pdl(HDRV)}$). Once the SW pin falls below $\sim V_{CC}/3$, Q2 begins to turn ON after an adaptive delay $t_{pdh(LDRV)}$.

Additionally, V_{GS} of Q1 is monitored. When $V_{GS(Q1)}$ is discharged below $\sim 1.3V$, a secondary adaptive delay is initiated, which results in Q2 being driven ON after $t_{pdh(LDF)}$, regardless of the SW state. This function is implemented to ensure C_{BOOT} is recharged after each switching cycle, particularly for cases where the power convertor is sinking current and the SW voltage does not fall below the $V_{CC}/3$ adaptive threshold. Secondary delay $t_{pdh(LDF)}$ is longer than $t_{pdh(LDRV)}$.

Application Information

Supply Capacitor Selection

For the supply input (V_{CC}) of the FAN5109, a local ceramic bypass capacitor is recommended to reduce the noise and to supply the peak current. Use at least a $1\mu F$, X7R or X5R capacitor. Keep this capacitor close to the FAN5109's V_{CC} and PGND pins.

Bootstrap Circuit

The bootstrap circuit uses a charge storage capacitor (C_{BOOT}) and an external diode, as shown in Figure 1. These components should be selected after the high-side MOSFET has been chosen. The required capacitance is determined using the following equation:

$$C_{BOOT} = \frac{Q_G}{\Delta V_{BOOT}} \quad (1)$$

where Q_G is the total gate charge of the high-side MOSFET, and ΔV_{BOOT} is the voltage droop allowed on the high-side MOSFET drive. For example, the Q_G of the FDD6696 MOSFET is about $35nC$ @ $12V_{GS}$. For an allowed droop of $\sim 300mV$, the required bootstrap capacitance is $100nF$. A good quality ceramic capacitor must be used.

The average diode forward current, $I_{F(AVG)}$, can be estimated by:

$$I_{F(AVG)} = Q_{GATE} \times F_{SW} \quad (2)$$

where F_{SW} is the switching frequency of the controller.

The peak surge current rating of the diode should be checked in-circuit, since this is dependent on the equivalent impedance of the entire bootstrap circuit, including the PCB traces.

Layout Considerations

Use the following general guidelines when designing printed circuit boards (see Figure 7 on the next page):

1. Trace out the high-current paths and use short, wide (>25 mil) traces to make these connections.
2. Connect the PGND pin of the FAN5109 as close as possible to the source of the lower MOSFET.

3. The V_{CC} bypass capacitor should be located as close as possible to V_{CC} and PGND pins.
4. Use vias to other layers when possible to maximize thermal conduction away from the IC.

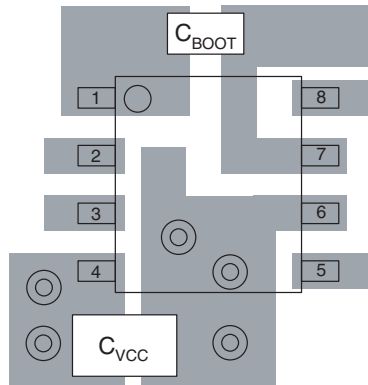


Figure 7. Recommended layout for SOIC-8 package (not to scale)

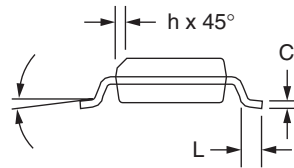
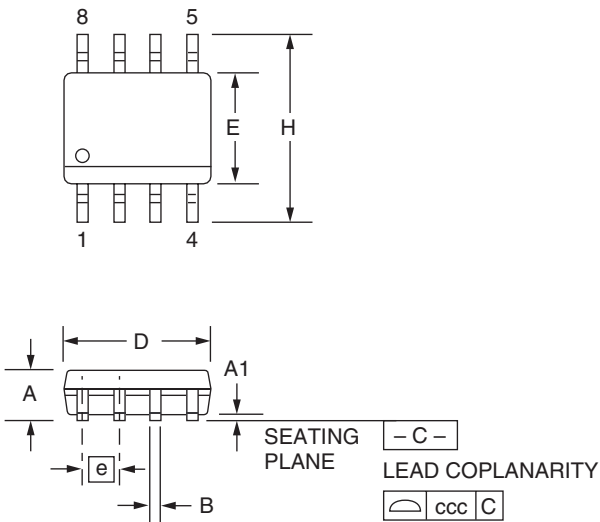
Mechanical Dimensions

0.150, 8 Lead SOIC Package

Symbol	Inches		Millimeters		Notes
	Min.	Max.	Min.	Max.	
A	.053	.069	1.35	1.75	
A1	.004	.010	0.10	0.25	
B	.013	.020	0.33	0.51	
C	.0075	.010	0.20	0.25	5
D	.189	.197	4.80	5.00	2
E	.150	.158	3.81	4.01	2
e	.050 BSC		1.27 BSC		
H	.228	.244	5.79	6.20	
h	.010	.020	0.25	0.50	
L	.016	.050	0.40	1.27	3
N	8		8		6
	0°	8°	0°	8°	
ccc	—	.004	—	0.10	

Notes:

1. Dimensioning and tolerancing per ANSI Y14.5M-1982.
2. "D" and "E" do not include mold flash. Mold flash or protrusions shall not exceed .010 inch (0.25mm).
3. "L" is the length of terminal for soldering to a substrate.
4. Terminal numbers are shown for reference only.
5. "C" dimension does not include solder finish thickness.
6. Symbol "N" is the maximum number of terminals.



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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

Rev. 116

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

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moschip.ru_9